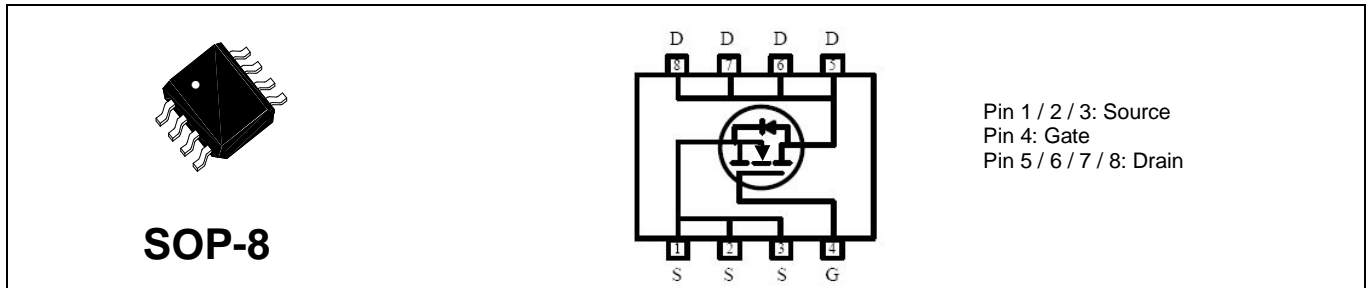


N-Channel Enhancement-Mode MOSFET (30V, 10A)

PRODUCT SUMMARY		
V_{DS}	I_D	$R_{DS(on)}$ (m-ohm) Max
30V	10A	13.5 @ $V_{GS} = 10V, I_D=10A$
		20 @ $V_{GS} = 4.5V, I_D=5A$

Features

- Advanced Trench Process Technology
- High Density Cell Design for Ultra Low On-Resistance
- Lead free product is acquired
- Surface mount Package



Absolute Maximum Ratings ($T_A=25^{\circ}C$, unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current @ $T_A=25^{\circ}C$	10	A
I_{DM}	Drain Current (Pulsed) ^a	50	A
P_D	Total Power Dissipation @ $T_A=25^{\circ}C$	2.5	W
T_j, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	50	$^{\circ}C/W$

a: Repetitive Rating: Pulse width limited by the maximum junction temperature.
b: 1-in² 2oz Cu PCB board